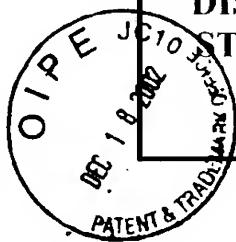


INFORMATION  
DISCLOSURE  
STATEMENT



Atty. Docket No.:	150.00880103	Serial No.:	10/045,345
Applicant(s):	Derderian et al.	Confirmation No.:	1310
Application Filing Date:	25 October 2001	Group:	2818
Information Disclosure Statement mailed:	December 12, 2002		

U.S. PATENT DOCUMENTS

Examiner Initial	Copy Enclosed	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
PD	X	6,337,238	01/08/02	Nakabayashi			

FOREIGN PATENT DOCUMENTS

Examiner Initial	Copy Enclosed	Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
		None						

OTHER DOCUMENTS (Including Authors, Title, Date, Pertinent Papers, etc.)

Examiner Initial	Copy Enclosed	Document Description
		None

DEC 20 2002  
U.S. PATENT & TRADEMARK OFFICE  
EXAMINER: PHUC T. DANG

EXAMINER	Date Considered
PHUC T. DANG	7/18/2003

\*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>INFORMATION DISCLOSURE STATEMENT</b>	<b>Atty. Docket No.:</b> 150.0088 0103	<b>Serial No.:</b> 10/045,345
	<b>Applicant(s):</b> Derderian et al.	<b>Confirmation No.:</b>
	<b>Filing Date:</b> 25 October 2001	<b>Group:</b> 2818

Examiner Initial	Copy Enclosed	Document Description	Stamp/Notes
PD		Nakamura et al., "Embedded DRAM Technology compatible to the 0.18 <sup>μ</sup> m high speed Logics by using Ru pillars in cell capacitors and peripheral vias," <i>IEEE</i> #3 IDS	FEB 15 2002 Patent high speed Logics 1/6/02
		Park et al., "Metallorganic Chemical Vapor Deposition of Ru and RuO <sub>2</sub> Using Ruthenocene Precursor and Oxygen Gas," <i>J. Electrochem. Soc.</i> , 147:203-209 (2000).	M. B. Larson
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